

General Purpose Transistor

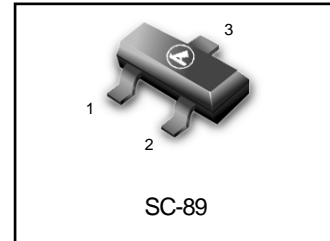
NPN Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SC-89 package which is designed for low power surface mount applications.

Features

- We declare that the material of product compliance with RoHS requirements.

LMBT2222ATT1G



ORDERING INFORMATION

Device	Maring	Shipping
LMBT2222ATT1G	1P	3000 / Tape & Reel
LMBT2222ATT3G	1P	10000 / Tape & Reel

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Collector–Emitter Voltage	V _{CEO}	40	Vdc
Collector–Base Voltage	V _{CBO}	75	Vdc
Emitter–Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	I _C	600	mAdc

THERMAL CHARACTERISTICS

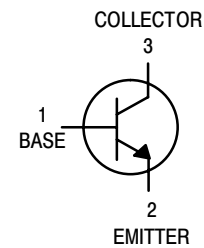
Characteristic	Symbol	Max	Unit
Total Device Dissipation (Note 1) T _A = 25°C	P _D	150	mW
Thermal Resistance, Junction–to–Ambient	R _{θJA}	833	°C/W
Operating and Storage Junction Temperature Range	T _J , T _{stg}	–55 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

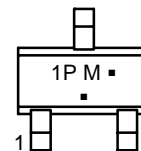
Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (Note 1) (I _C = 1.0 mAdc, I _B = 0)	V _{(BR)CEO}	40	–	Vdc
Collector–Base Breakdown Voltage (I _C = 10 μAdc, I _E = 0)	V _{(BR)CBO}	75	–	Vdc
Emitter–Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0)	V _{(BR)EBO}	6.0	–	Vdc
Base Cutoff Current (V _{CE} = 60 Vdc, V _{EB} = 3.0 Vdc)	I _{BL}	–	20	nAdc
Collector Cutoff Current (V _{CE} = 60 Vdc, V _{EB} = 3.0 Vdc)	I _{CEX}	–	100	nAdc



MARKING DIAGRAM



- 1P = Specific Device Code
- M = Date Code
- = Pb–Free Package

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ON CHARACTERISTICS (Note 2)

DC Current Gain ($I_C = 0.1 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$) ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$) ($I_C = 10 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$) ($I_C = 150 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$) ($I_C = 500 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$)	H_{FE}	35 50 75 100 40	- - - - -	-
Collector–Emitter Saturation Voltage ($I_C = 150 \text{ mAdc}$, $I_B = 15 \text{ mAdc}$) ($I_C = 500 \text{ mAdc}$, $I_B = 50 \text{ mAdc}$)	$V_{CE(sat)}$	- -	0.3 1.0	Vdc
Base –Emitter Saturation Voltage ($I_C = 150 \text{ mAdc}$, $I_B = 15 \text{ mAdc}$) ($I_C = 500 \text{ mAdc}$, $I_B = 50 \text{ mAdc}$)	$V_{BE(sat)}$	0.6 -	1.2 2.0	Vdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product ($I_C = 20 \text{ mAdc}$, $V_{CE} = 20 \text{ Vdc}$, $f = 100 \text{ MHz}$)	f_T	250	-	MHz
Output Capacitance ($V_{CB} = 10 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)	C_{obo}	-	8.0	pF
Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}$, $I_C = 0$, $f = 1.0 \text{ MHz}$)	C_{ibo}	-	30	pF
Input Impedance ($V_{CE} = 10 \text{ Vdc}$, $I_C = 10 \text{ mAdc}$, $f = 1.0 \text{ kHz}$)	h_{ie}	0.25	1.25	k Ω
Voltage Feedback Ratio ($V_{CE} = 10 \text{ Vdc}$, $I_C = 10 \text{ mAdc}$, $f = 1.0 \text{ kHz}$)	h_{re}	-	4.0	$\times 10^{-4}$
Small–Signal Current Gain ($V_{CE} = 10 \text{ Vdc}$, $I_C = 10 \text{ mAdc}$, $f = 1.0 \text{ kHz}$)	h_{fe}	75	375	-
Output Admittance ($V_{CE} = 10 \text{ Vdc}$, $I_C = 10 \text{ mAdc}$, $f = 1.0 \text{ kHz}$)	h_{oe}	25	200	μmhos
Noise Figure ($V_{CE} = 10 \text{ Vdc}$, $I_C = 100 \mu\text{Adc}$, $R_S = 1.0 \text{ k ohms}$, $f = 1.0 \text{ kHz}$)	NF	-	4.0	dB

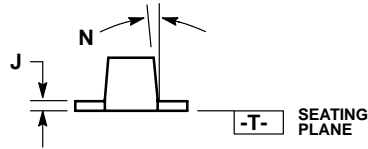
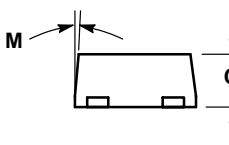
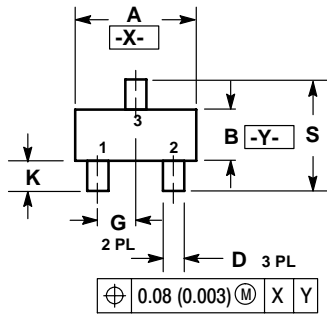
SWITCHING CHARACTERISTICS

Delay Time	$(V_{CC} = 3.0 \text{ Vdc}$, $V_{BE} = -0.5 \text{ Vdc}$, $I_C = 150 \text{ mAdc}$, $I_{B1} = 15 \text{ mAdc}$)	t_d	-	10	ns
Rise Time		t_r	-	25	
Storage Time	$(V_{CC} = 30 \text{ Vdc}$, $I_C = 150 \text{ mAdc}$, $I_{B1} = I_{B2} = 15 \text{ mAdc}$)	t_s	-	225	ns
Fall Time		t_f	-	60	

1. Device mounted on FR4 glass epoxy printed circuit board using the minimum recommended footprint.
2. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

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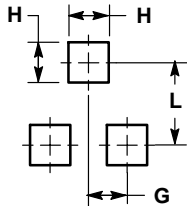
SC-89



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 463C-01 OBSOLETE, NEW STANDARD 463C-02.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.60	1.70	0.059	0.063	0.067
B	0.75	0.85	0.95	0.030	0.034	0.040
C	0.60	0.70	0.80	0.024	0.028	0.031
D	0.23	0.28	0.33	0.009	0.011	0.013
G	0.50 BSC			0.020 BSC		
H	0.53 REF			0.021 REF		
J	0.10	0.15	0.20	0.004	0.006	0.008
K	0.30	0.40	0.50	0.012	0.016	0.020
L	1.10 REF			0.043 REF		
M	---	---	10°	---	---	10°
N	---	---	10°	---	---	10°
S	1.50	1.60	1.70	0.059	0.063	0.067


RECOMMENDED PATTERN OF SOLDER PADS